

Excellent Integrated System Limited

Stocking Distributor

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Vishay/Siliconix SI7856ADP-T1-E3

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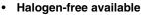
Si7856ADP

Vishay Siliconix

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)		
30	0.0037 at V _{GS} = 10 V	25	39		
	0.0048 at V _{GS} = 4.5 V	23	39		

FEATURES





 Optimized for "Low Side" Synchronous Rectifier Operation

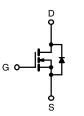


New Low Thermal Resistance PowerPAK[®] Package with Low 1.07 mm Profile

100 % R_g Tested

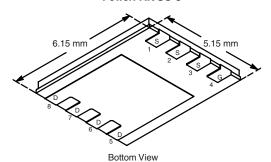
APPLICATIONS

- DC/DC Converters
- · Synchronous Rectifiers



N-Channel MOSFET

PowerPAK SO-8



Ordering Information: Si7856ADP-T1

Si7856ADP-T1-E3 (Lead (Pb)-free)

Si7856ADP-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	$T_A = 25 ^{\circ}C$, unles	ss otherwise n	oted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T _{.I} = 150 °C) ^a	T _A = 25 °C	I _D	25	15	Α
Continuous Diain Current (1) = 150 °C)	T _A = 70 °C		20	12	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	60		Α
Continuous Source Current (Diode Conduction) ^a		I _S	4.5	1.6	
Maximum Davier Dissination	T _A = 25 °C	P _D	5.4	1.9	W
Maximum Power Dissipation ^a	T _A = 70 °C		3.4	1.2	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature)b, c		-	260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	t ≤ 10 s	- R _{thJA}	18	23	°C/W	
Maximum Junction-to-Ambient	Steady State		50	65		
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.0	1.5		

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.

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Datasheet of SI7856ADP-T1-E3 - MOSFET N-CH 30V 15A PPAK SO-8

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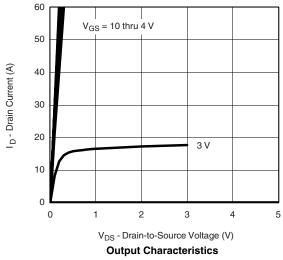
Parameter	Symbol	Test Conditions		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.0		3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zava Cata Valtaria Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	V _{DS} = 30 V, V _{GS} = 0 V V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C		1	μΑ	
Zero Gate Voltage Drain Current		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C			5		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α	
	Ь	V _{GS} = 10 V, I _D = 25 A	0.0029 0.00		0.0037		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 19 \text{ A}$		0.0036	0.0048	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 25 A		95		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 2.9 A, V _{GS} = 0 V		0.7	1.1	V	
Dynamic ^b							
Total Gate Charge	Q_g			39	55		
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 25 \text{ A}$		13.5		nC	
Gate-Drain Charge	Q_{gd}			11.5			
Gate Resistance	R_g		0.5	1.0	1.5	Ω	
Turn-On Delay Time	t _{d(on)}			21	35		
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		15	25	ns	
Turn-Off Delay Time	t _{d(off)}	$t_{d(off)}$ $I_D \cong 1 \text{ A, } V_{GEN} = 10 \text{ V, } R_G = 6 \Omega$		100	150		
Fall Time	t _f			30	45		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.9 A, di/dt = 100 A/μs		50	80		

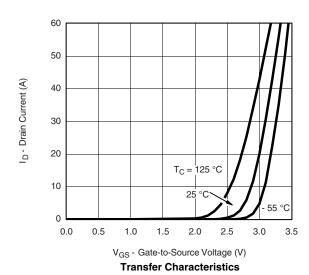
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted









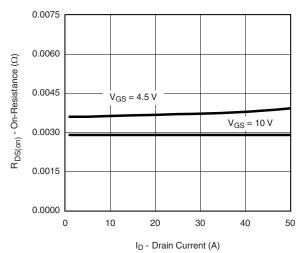
V_{GS} - Gate-to-Source Voltage (V)

Is - Source Current (A)

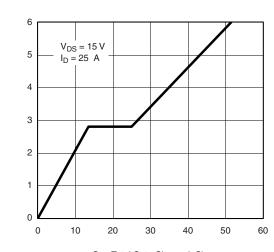
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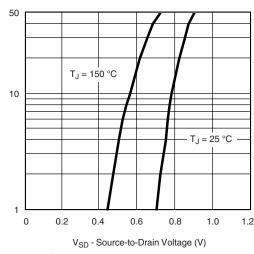
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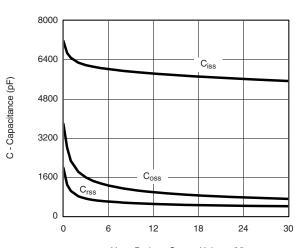
On-Resistance vs. Drain Current



Q_q - Total Gate Charge (nC) **Gate Charge**

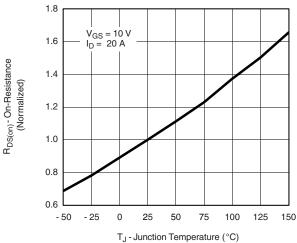


Source-Drain Diode Forward Voltage

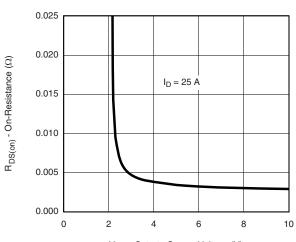


V_{DS} - Drain-to-Source Voltage (V)





On-Resistance vs. Junction Temperature



V_{GS} - Gate-to-Source Voltage (V) On-Resistance vs. Gate-to-Source Voltage

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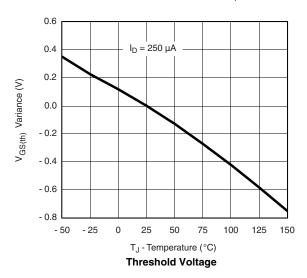


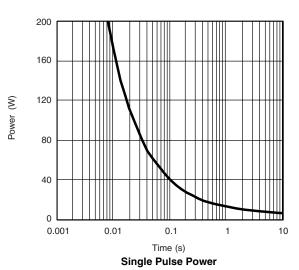
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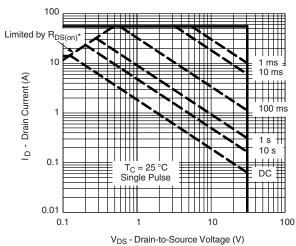
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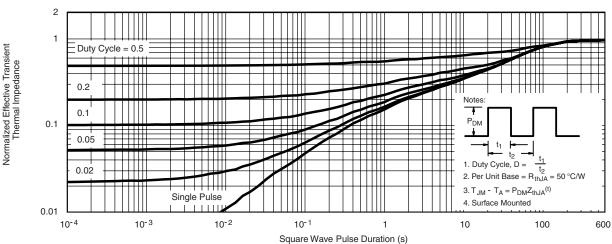








* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified **Safe Operating Area Junction-to-Case**



Normalized Thermal Transient Impedance, Junction-to-Ambient

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Datasheet of SI7856ADP-T1-E3 - MOSFET N-CH 30V 15A PPAK SO-8

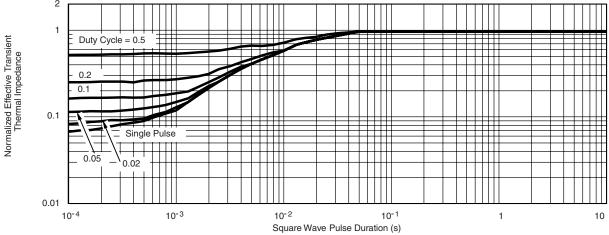
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Si7856ADP

Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?73157.

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Datasheet of SI7856ADP-T1-E3 - MOSFET N-CH 30V 15A PPAK SO-8

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